YJL3134KBX

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

ŏ V_{DS}	20 V
ŏ I_D	0.5 A
ŏ $R_{DS(ON)}$(at V_{GS}=4.5V)	ˎ 300 mohm
ŏ $R_{DS(ON)}$(at V_{GS}=2.5V)	ˎ 400 mohm
ŏ $R_{DS(ON)}$(at V_{GS}=1.8V)	ˎ 950 mohm

ŏ ESD Protected Up to 2.0KV (HBM)

General Description

ŏ Trench Power LV MOSFET technology
ŏ High Power and current handing capability
ŏ Moisture Sensitivity Level 1
ŏ Epoxy Meets UL 94 V-0 Flammability Rating
ŏ Halogen Free

Applications

ŏ PWM application
ŏ Load switch

ӳ **Absolute Maximum Ratings** (T_A=25 Ṇ unless otherwise noted)

ý **Electrical Characteristics** (T$_J$=25Ņ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						

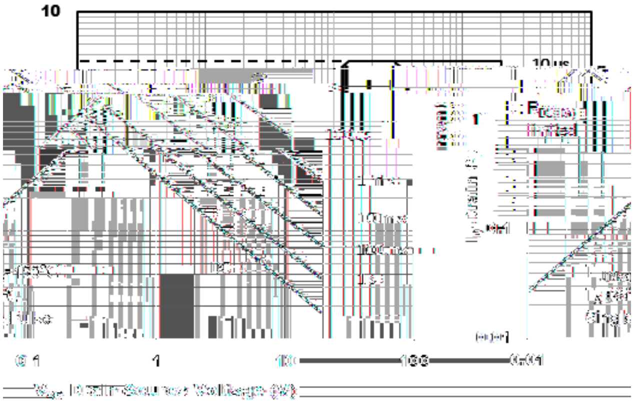


Figure7. Safe Operation Area

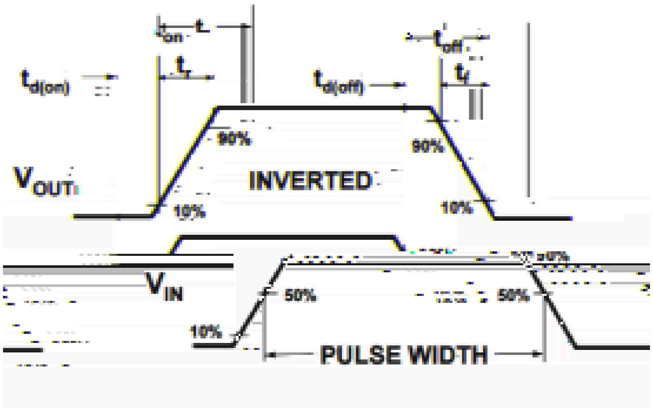
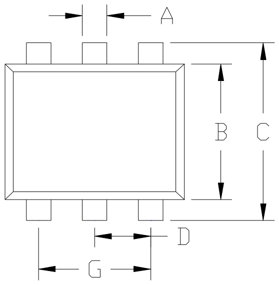
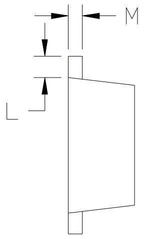


Figure8. Switching wave

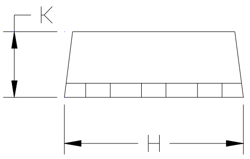
√SOT-563 Package information



TOP VIEW



SIDE VIEW



SIDE VIEW

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